

2N6989, 2N6989U, 2N6990

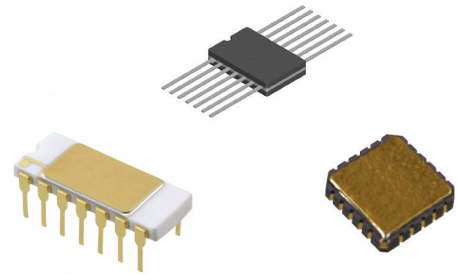


Multiple (Quad) NPN Silicon Dual In-Line And Flatpack Switching Transistor

Rev. V3

Features

- Available in JAN, JANTX, JANTXV, JANS and JANSR per MIL-PRF-19500/559
- TO-116, 20 PIN Leadless (U) and 14 PIN Flat Pack package types
- Radiation Tolerant Levels M, D, P, L, and R



Electrical Characteristics

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Off Characteristics					
Collector - Emitter Breakdown Voltage	$I_C = 10 \text{ mA dc}$	$V_{(BR)CEO}$	V dc	50	—
Collector - Base Cutoff Current	$V_{CB} = 75 \text{ V dc}$ $V_{CB} = 60 \text{ V dc}$	I_{CBO1}	$\mu\text{A dc}$	—	10
		I_{CBO2}	nA dc	—	10
Emitter - Base Cutoff Current	$V_{EB} = 6.0 \text{ V dc}$ $V_{EB} = 4.0 \text{ V dc}$	I_{EBO1}	$\mu\text{A dc}$	—	10
		I_{EBO2}	nA dc	—	10
On Characteristics					
Forward Current Transfer Ratio	$V_{CE} = 10 \text{ V dc}; I_C = 0.1 \text{ mA dc}$	h_{FE}	-	50	325
	$V_{CE} = 10 \text{ V dc}; I_C = 1.0 \text{ mA dc}$			75	
	$V_{CE} = 10 \text{ V dc}; I_C = 10 \text{ mA dc}$			100	
	$V_{CE} = 10 \text{ V dc}; I_C = 150 \text{ mA dc}$			100	
	$V_{CE} = 10 \text{ V dc}; I_C = 500 \text{ mA dc}$			30	
Collector - Emitter Saturation Voltage	$I_C = 150 \text{ mA dc}; I_B = 15 \text{ mA dc}$	$V_{CE(SAT)1}$ $V_{CE(SAT)2}$	V dc	—	0.3
	$I_C = 500 \text{ mA dc}; I_B = 50 \text{ mA dc}$				1.0
Base - Emitter Saturation Voltage	$I_C = 150 \text{ mA dc}; I_B = 15 \text{ mA dc}$	$V_{BE(SAT)1}$ $V_{BE(SAT)2}$	V dc	0.6	1.2
	$I_C = 500 \text{ mA dc}; I_B = 50 \text{ mA dc}$				2.0
Dynamic Characteristics					
Magnitude of Common Small-Signal Short-Circuit Forward Current Transfer Ratio	$V_{CE} = 10 \text{ V dc}; I_C = 20 \text{ mA dc}; f = 100 \text{ MHz}$	$ h_{fe} $		2.5	10.0
Small-Signal Short-Circuit Forward Current Transfer Ratio	$V_{CE} = 10 \text{ V dc}; I_C = 1 \text{ mA dc}; f = 1 \text{ kHz}$	h_{fe}		50	
Open Circuit Output Capacitance	$V_{CB} = 10 \text{ V dc}; I_E = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{obo}	pF	—	8.0
Input Capacitance (Output Open-Circuited)	$V_{EB} = 0.5 \text{ V dc}; I_C = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{ibo}	pF	—	25

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Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Base Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CB} = 60 \text{ V dc}$	I_{CBO3}	$\mu\text{A dc}$	—	10
Forward-Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $V_{CE} = 10 \text{ V dc}; I_C = 10 \text{ mA dc}$	h_{FE6}		35	
Transistor to Transistor Resistance	$ V_{T-T} = 500 \text{ V dc}$	R_{T-T}	ohms	10^{10}	—
Switching Characteristics					
Turn-On Time (saturated)	See figure 14 of MIL-PRF-19500/559	t_{on}	ns	—	35
Turn-Off Time (saturated)	See figure 15 of MIL-PRF-19500/559	t_{off}	ns	—	300

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Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	$V_{CEO}^{(4)}$	50 V dc
Collector - Base Voltage	$V_{CBO}^{(4)}$	75 V dc
Emitter - Base Voltage	$V_{EBO}^{(4)}$	6.0 V dc
Collector Current	I_C	800 mA dc
Total Power Dissipation (2) @ $T_A = +25^\circ\text{C}$ 2N6989 2N6989U 2N6990	$P_T^{(2)}$	1.5 W 1.0 W 1.0 W
Total Power Dissipation (2) @ $T_{A(AM)} = +25^\circ\text{C}$ 2N6990	$P_T^{(2)}$	1.0 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to $+200^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Ambient (3) 2N6989 2N6989U 2N6990	$R_{\theta JA}$	85°C/W 160°C/W 175°C/W
Thermal Resistance, Junction to Ambient (3) 2N6989 2N6989U 2N6990	$R_{\theta JA (AM)}$	N/A N/A 23°C/W

- (1) Maximum voltage between transistors shall be ≥ 500 V dc.
- (2) For derating, see figures 6, 7, 8 and 9 of MIL-PRF-19500/559. Ratings shall apply to total package.
- (3) For thermal impedance curves, see figures 10, 11, 12 and 13 of MIL-PRF-19500/559
- (4) Ratings apply to each transistor in the array.

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Outline Drawing 2N6989

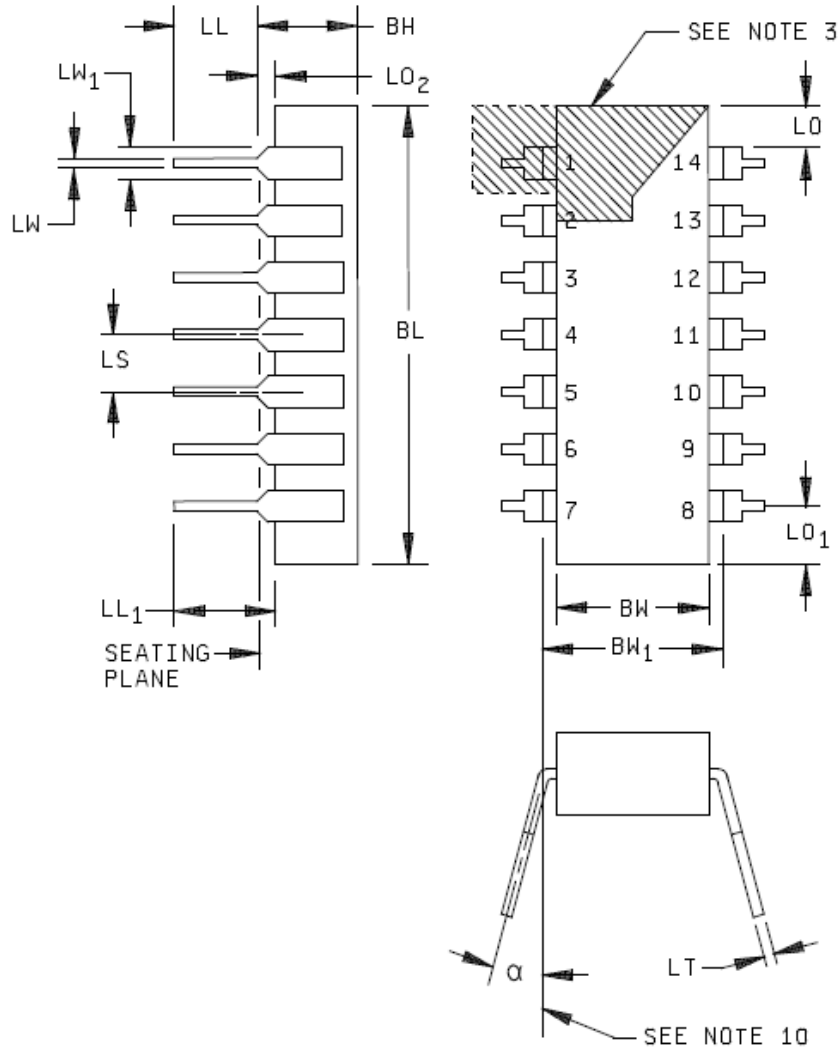


FIGURE 1. Dimensions and configuration for type 2N6989.

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Outline Dimensions 2N6989

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BH		.200		5.08	
LW	.014	.023	0.36	0.58	10
LW ₁	.030	.070	0.76	1.78	4, 10
LT	.008	.015	0.20	0.38	10
BL		.785		19.94	6
BW	.220	.310	5.59	7.87	6
BW ₁	.290	.320	7.37	8.13	9

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
LS	.100 BSC		2.54 BSC		7, 11
LL	.125	.200	3.18	5.08	
LL ₁	.150		3.81		
LO	.005		0.13		8
LO ₁		.098		2.49	8
LO ₂	.015	.060	0.38	1.52	5
α	0°	15°	0°	15°	

NOTES:

- Dimensions are in inches.
- Millimeters are given for general information only.
- Index area: A notch or pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- The minimum limit for dimension LW₁ may be .023 inch (0.58 mm) for leads number 1, 7, 8, and 14 only.
- Dimension LO₂ shall be measured from the seating plane to the base plane.
- This dimension allows for off-center lid, meniscus, and glass overrun.
- The basic pin spacing is .100 inch (2.54 mm) between centerlines. Each pin centerline shall be located within ± 0.010 inch (0.25 mm) of its exact longitudinal position relative to pins 1 and 14.
- Applies to all four corners (leads number 1, 7, 8, and 14).
- Lead center when α is 0 degrees. BW₁ shall be measured at the centerline of the leads.
- All leads.
- Twelve spaces.
- No organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
- In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 1. Dimensions and configuration for type 2N6989 - Continued.

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Outline Drawing 2N6990

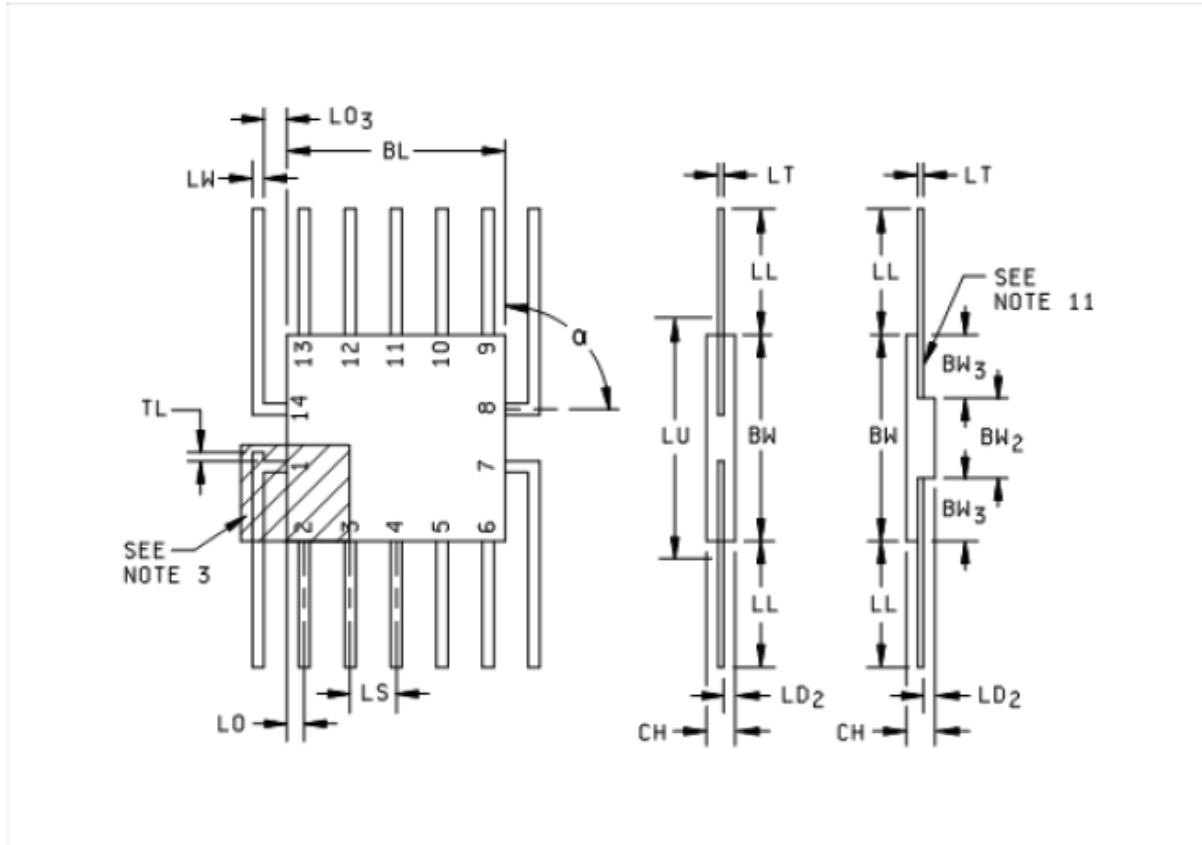


FIGURE 2. Physical dimensions for type 2N6990.

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Outline Dimensions 2N6990

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CH	.030	.115	0.76	2.92	
LW	.010	.019	0.25	0.48	7
TL	.008	.015	0.20	0.38	12
BL		.280		7.11	5
BW	.240	.260	6.10	6.60	
LU		.290		7.37	5
BW ₂	.125		3.18		

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BW ₃	.030		0.76		
LS	.050 BSC		1.27 BSC		6, 8
LT	.003	.006	0.076	0.152	7
LL	.250	.370	6.35	9.40	
LD ₂	.005	.040	0.13	1.02	4
LO	.005		0.13		9, 10
LO ₃	.004		0.10		13
α	30°	90°	30°	90°	14

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Index area: A notch or pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternatively, a tab (dim TL) may be used to identify pin one.
4. Dimension LD₂ shall be measured at the point of exit of the lead from the body.
5. This dimension allows for off-center lid, meniscus, and glass overrun.
6. The basic pin spacing is .050 inch (1.27 mm) between centerlines. Each pin centerline shall be located within ± 0.005 inch (0.13 mm) of its exact longitudinal position relative to pins 1 and 14.
7. All leads: Increase maximum limit by .003 inch (0.08 mm) measured at the center of the flat when the lead finish is solder.
8. Twelve spaces.
9. Applies to all four corners (leads number 2, 6, 9, and 13).
10. Dimension LO may be .000 inch (0.00 mm if leads number 2, 6, 9, and 13) bend toward the cavity of the package within one lead width from the point of entry of the lead into the body or if the leads are brazed to the metallized ceramic body.
11. No organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
12. Optional, see note 1. If a pin one identification mark is used in addition to this tab, the minimum limit of dimension TL does not apply.
13. Applies to leads number 1, 7, 8, and 14.
14. Lead configuration is optional within dimension BW except dimensions LW and LT apply.
15. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.
16. Pins 1, 7, 8, and 14 are collectors.
17. Pins 2, 6, 9, and 13 are bases.
18. Pins 3, 5, 10, and 12 are emitters.
19. Pins 4 and 11 are no contacts.

FIGURE 2. Physical dimensions for type 2N6990 - Continued.

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Outline Drawing

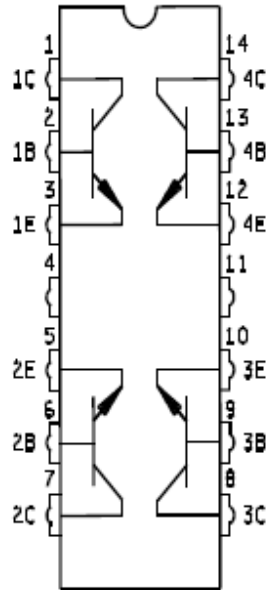


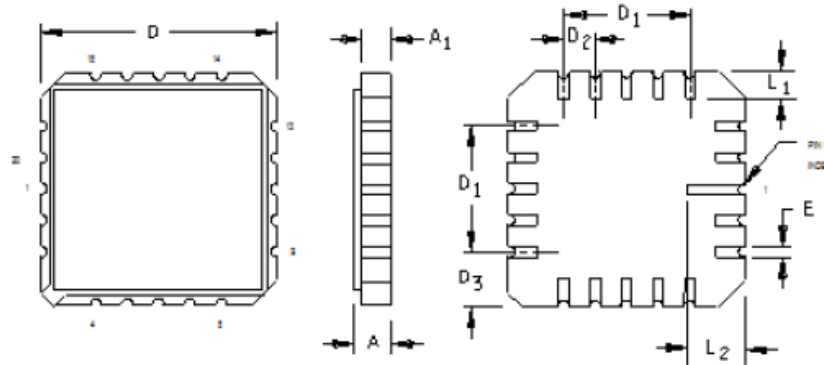
FIGURE 3. Schematic and terminal connections for type 2N6989 and 2N6990.

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Outline Drawing 2N6989U



Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
A	.073	.085	1.85	2.16
A ₁	.063	.075	1.60	1.91
D	.345	.355	8.76	9.02
D ₁	.195	.205	4.95	5.21
D ₂	.050 TYP		1.27 TYP	
D ₃	.070	.080	1.78	2.03
E	.025 REF		0.64 REF	
L ₁	.050 REF for pins 2 through 20		1.27 REF for pins 2 through 20	
L ₂	.080	.090	2.03	2.29

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Unless otherwise specified, tolerance is ± 0.005 inch (0.13 mm).
4. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 4. Physical dimensions for type 2N6989U.

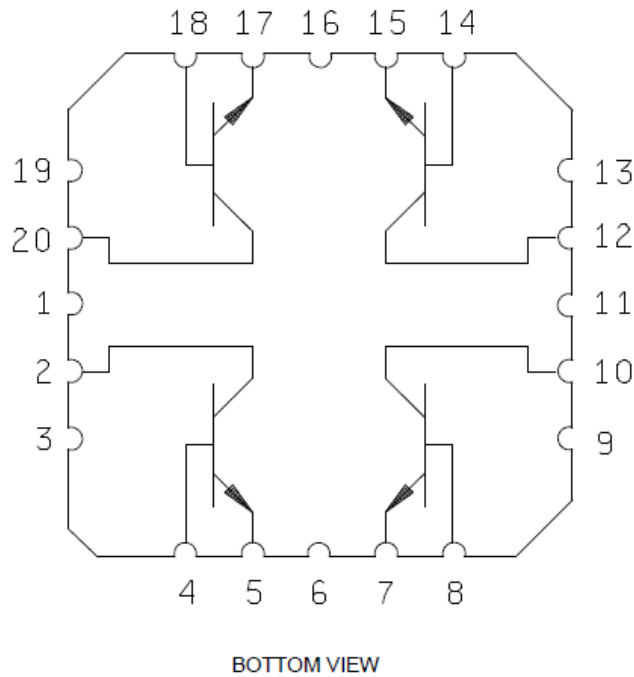
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Outline Drawing



	Pin numbers		
	Base	Collector	Emitter
First transistor	4	2	5
Second transistor	8	10	7
Third transistor	14	12	15
Fourth transistor	18	20	17

FIGURE 5. Schematic and terminal connections for type 2N6989U.

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